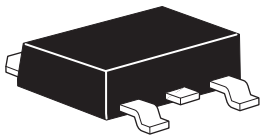
ZXMN4A06K
40V N-channel enhancement mode MOSFET

Summary

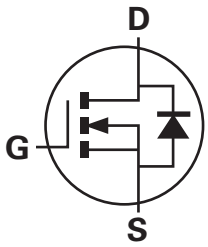


$V_{(BR)DSS}$= -40V; $R_{DS(ON)}$ = 0.05Ω; I_D = 10.9A

Description

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

Features



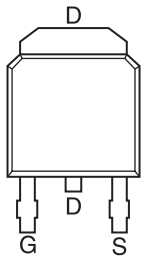
- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- DPAK package

Applications

- DC - DC converters
- Audio output stages
- Relay and solenoid driving
- Motor control

Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN4A06KTC	13	16	2,500



Pinout - Top view

Device marking

ZXMN
4A06

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Drain-source voltage	V_{DSS}	40	V
Gate-source voltage	V_{GS}	±20	V
Continuous drain current: V_{GS}=10V; T_A=25°C (b) V_{GS}=10V; T_A=70°C (b) V_{GS}=10V; T_A=25°C (a)	I_D	 10.9 8.7 7.2	 A A A
Pulsed drain current (c)	I_{DM}	35.3	A
Continuous source current (body diode) (b)	I_S	10.8	A
Pulsed source current (body diode) (c)	I_{SM}	35.3	A
Power dissipation at T_A=25°C (a) Linear derating factor	P_D	4.2 33.6	W mW/°C
Power dissipation at T_A=25°C (b) Linear derating factor	P_D	9.5 76	W mW/°C
Power dissipation at T_A=25°C (d) Linear derating factor	P_D	2.15 17.2	W mW/°C
Operating and storage temperature range	T_j:T_{stg}	-55 to +150	°C

Thermal resistance

Parameter	Symbol	Value	Unit
Junction to ambient (a)	$R_{\Theta JA}$	30	°C/W
Junction to ambient (b)	$R_{\Theta JA}$	13.2	°C/W
Junction to ambient (d)	$R_{\Theta JA}$	58	°C/W

NOTES:

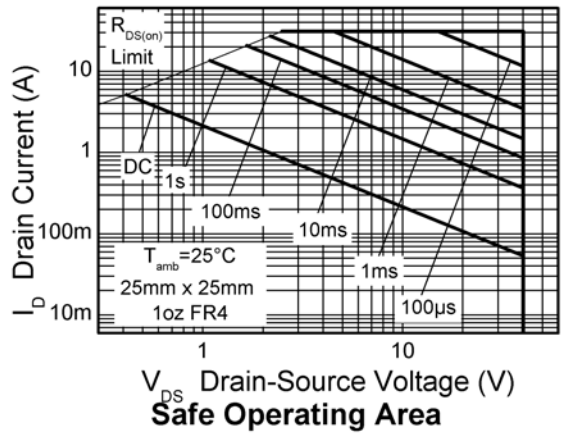
(a) For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.

(b) For a device surface mounted on FR4 PCB measured at t 10 sec.

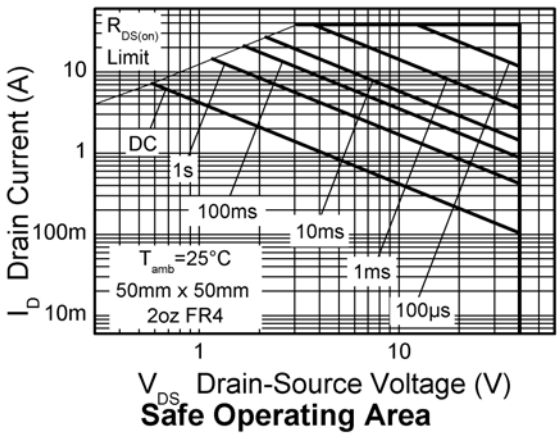
(c) Repetitive rating 50mm x 50mm x 1.6mm FR4 PCB, D=0.02 pulse width=300 s - pulse width limited by maximum junction temperature.

(d) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

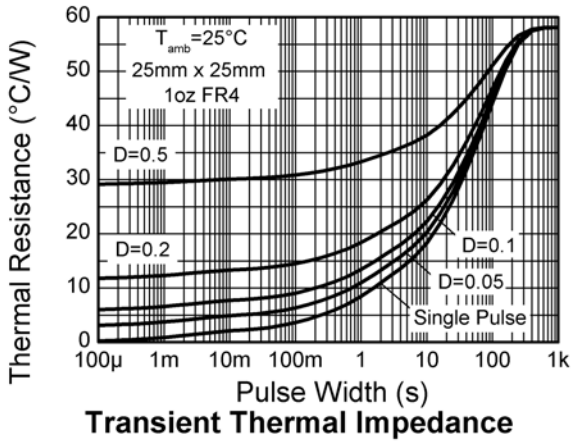
Characteristics



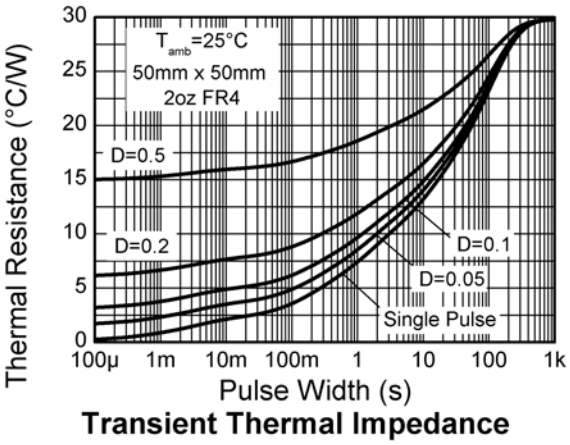
Safe Operating Area



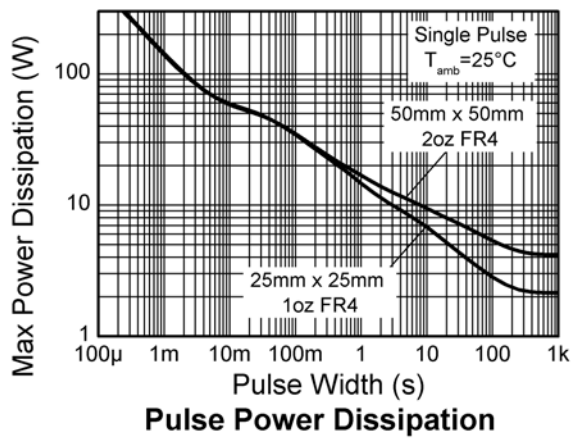
Safe Operating Area



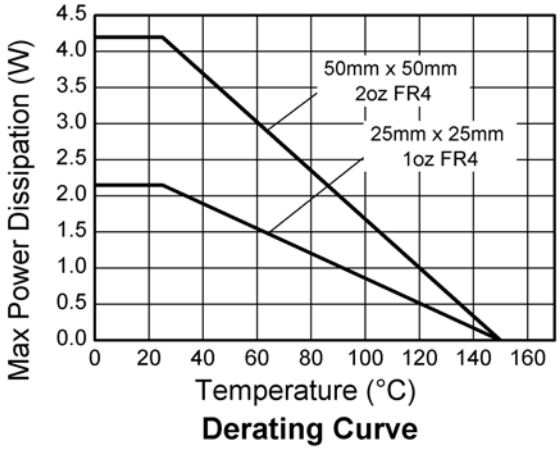
Transient Thermal Impedance



Transient Thermal Impedance



Pulse Power Dissipation



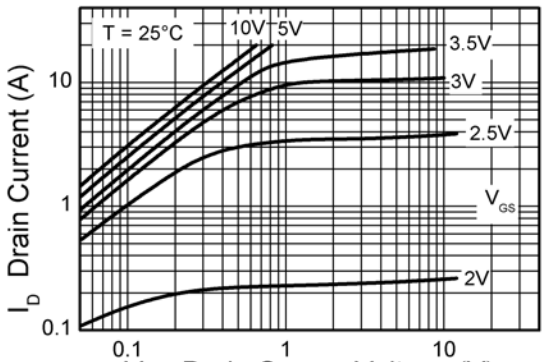
Derating Curve

Electrical characteristics (at T_A = 25°C unless otherwise stated)

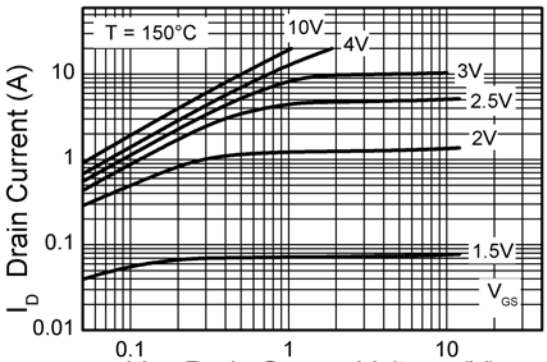
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Static						
Drain-source breakdown voltage	$V_{(BR)DSS}$	40			V	I_D=250μA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}			1	μA	V_{DS}=40V, V_{GS}=0V
Gate-body leakage	I_{GSS}			100	nA	V_{GS}=±20V, V_{DS}=0V
Gate-source threshold voltage	$V_{GS(th)}$	1.0			V	I_D=250μA, V_{DS}= V_{GS}
Static drain-source on-state resistance (*)	$R_{DS(on)}$			0.050 0.075	Ω Ω	V_{GS}=10V, I_D=4.5A V_{GS}=4.5V, I_D=3.2A
Forward transconductance(‡)	g_{fs}		11.5		S	V_{DS}=15V,I_D=4.5A
Dynamic (‡)						
Input capacitance	C_{iss}		827		pF	V_{DS}=20 V, V_{GS}=0V, f=1MHz
Output capacitance	C_{oss}		133		pF	
Reverse transfer capacitance	C_{rss}		84		pF	
Switching (†) (‡)						
Turn-on delay time	$t_{d(on)}$		3.2		ns	V_{DD} =20V, I_D=1A R_G=6.0Ω, V_{GS}=10V (refer to test circuit)
Rise time	t_r		3.8		ns	
Turn-off delay time	$t_{d(off)}$		23.3		ns	
Fall time	t_f		10.9		ns	
Total gate charge	Q_g		17.1		nC	V_{DS}=20V,V_{GS}=10V, I_D=4.5A (refer to test circuit)
Gate-source charge	Q_{gs}		2.41		nC	
Gate-drain charge	Q_{gd}		3.4		nC	
Source-drain diode						
Diode forward voltage(*)	V_{SD}		0.83	0.95	V	T_J=25°C, I_S=4.5A, V_{GS}=0V
Reverse recovery time(†)	t_{rr}		16		ns	T_J=25°C, I_F=4A, di/dt= 100A/μs
Reverse recovery charge(‡)	Q_{rr}		9		nC	

NOTES:
(*) Measured under pulsed conditions. Width ≤300μs. Duty cycle ≤2%.
(†) Switching characteristics are independent of operating junction temperature.
(‡) For design aid only, not subject to production testing.

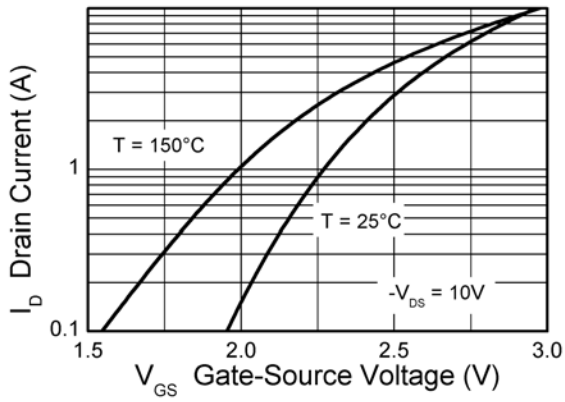
Typical charactersitics



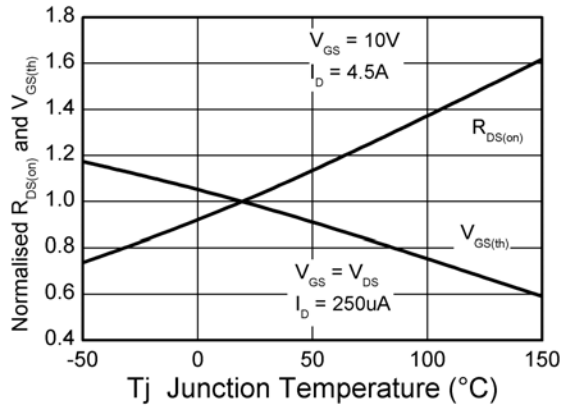
Output Characteristics



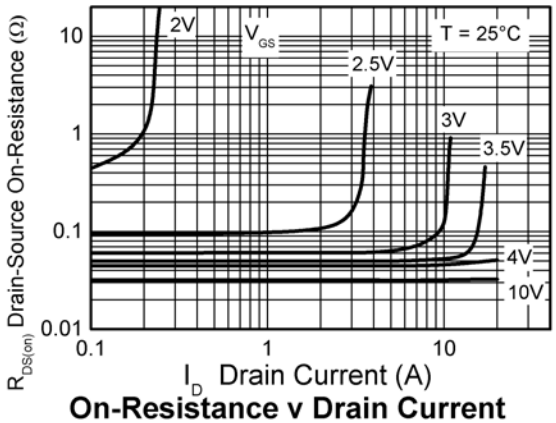
Output Characteristics



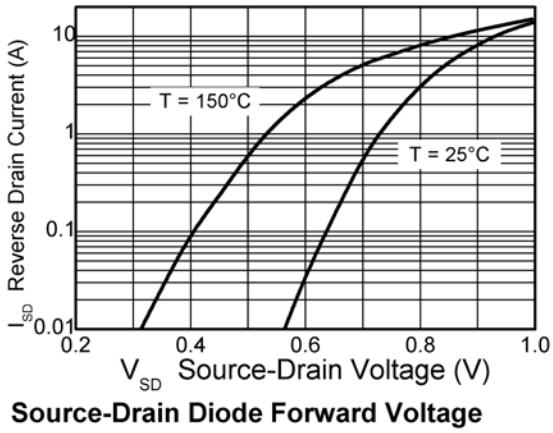
Typical Transfer Characteristics



Normalised Curves v Temperature

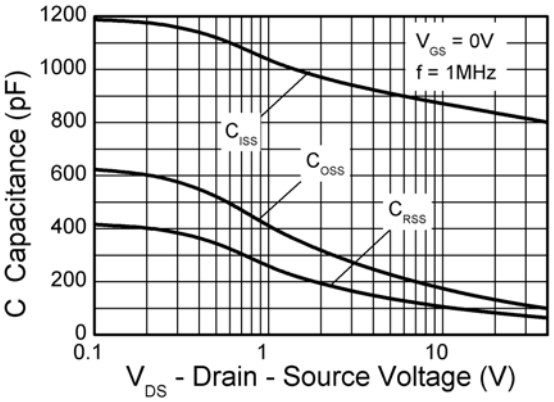


On-Resistance v Drain Current

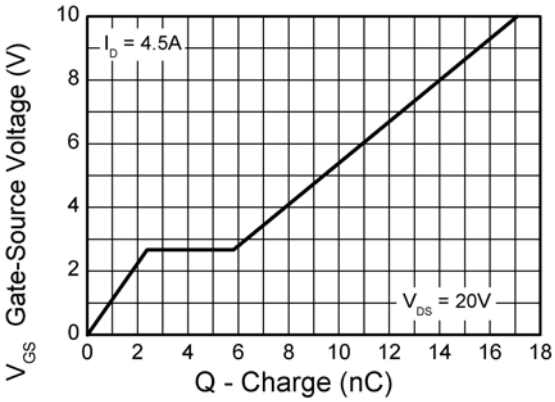


Source-Drain Diode Forward Voltage

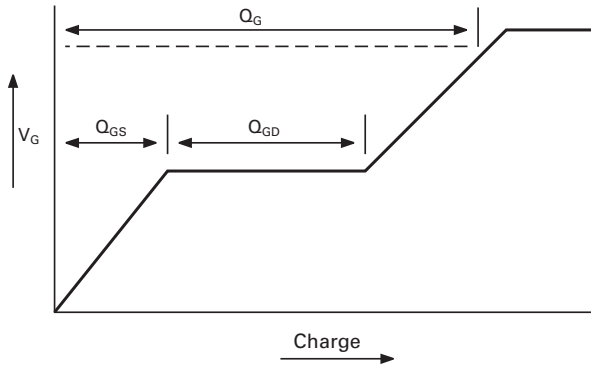
Typical characteristics



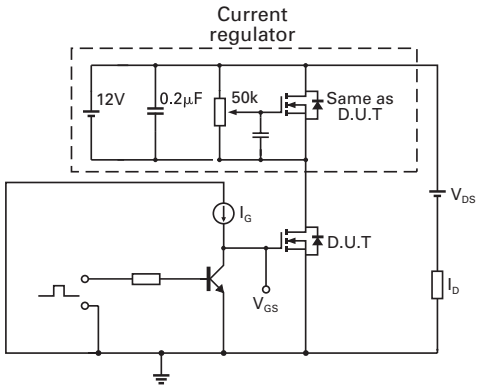
Capacitance v Drain-Source Voltage



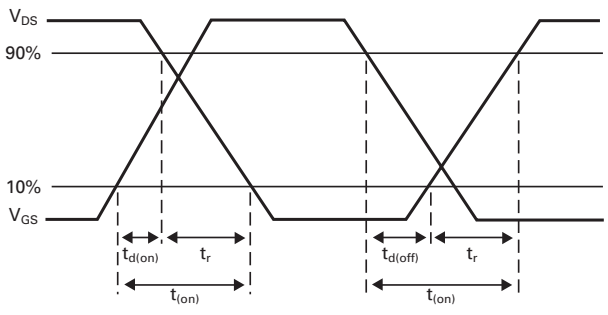
Gate-Source Voltage v Gate Charge



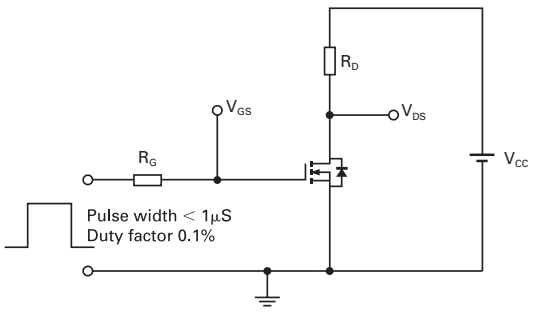
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms



Switching time test circuit

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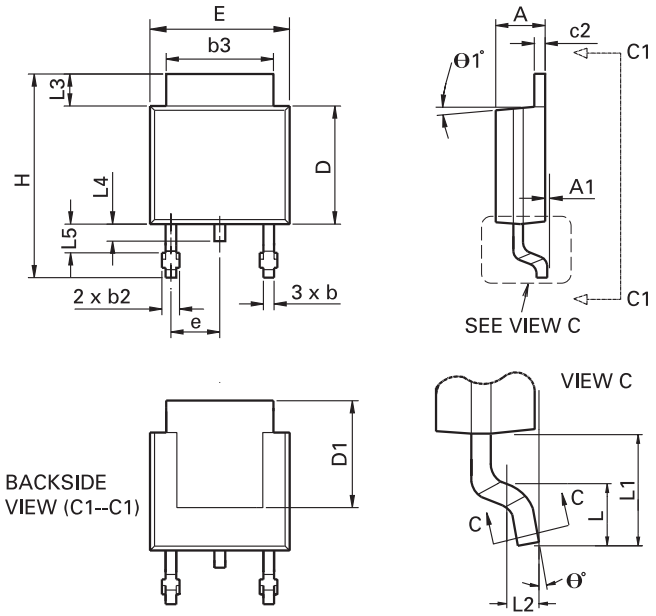
Package details - DPAK



Package dimensions

Dim.	Inches		Millimeters		Dim.	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.086	0.094	2.18	2.39	e	0.090 BSC		2.29 BSC	
A1	-	0.005	-	0.127	H	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
c	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	θ1°	0°	10°	0°	10°
E	0.250	0.265	6.35	6.73	θ°	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-

Note: Controlling dimensions are in inches. Approximate dimensions are provided in millimeters

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